

3-5 Jun 2020



36th RD50 Workshop (CERN - - online Workshop)

Defect Characterization

Wednesday 3 June

10:00

Defect Characterization: Defect and Material Characterization

Session | Location: Virtual meeting at CERN

10:00-10:20

Quantum characteristics of electron and hole quasiparticles in silicon defects

Speaker

Prof. Darius Abramavicius

10:20-10:40

Electron mobility dependence on neutron and electron irradiation fluence in Si

Speaker

Prof. Juozas Vaitkus

10:40-11:00

Update on Radiation damage investigation of epitaxial P type Silicon using Schottky / pn junctions and LGAD - GaN activities at RAL

Speaker

Enrico Giulio Villani

11:00-11:20 Break

11:20-11:40 DLTS and TSC techniques: A brief introduction

Speaker

Anja Himmerlich

11:40-12:00

Defect characterization in boron doped silicon sensors after exposure to protons, neutrons and electrons

Speaker

Yana Gurimskaya

12:00-12:20 DLTS studies on as irradiated PiN diodes of different resistivity

Speaker

Ioana Pintilie

12:20-12:40 Discussion Session: Defect Characterization & Acceptor Removal

Speaker

Ioana Pintilie

13:00